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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	ARM® Cortex®-A53
Number of Cores/Bus Width	8 Core, 64-Bit
Speed	1.6GHz
Co-Processors/DSP	-
RAM Controllers	DDR4
Graphics Acceleration	-
Display & Interface Controllers	-
Ethernet	10GbE (2), 1GbE (8)
SATA	SATA 6Gbps (1)
USB	USB 3.0 (2) + PHY
Voltage - I/O	-
Operating Temperature	-40°C ~ 105°C
Security Features	Secure Boot, TrustZone®
Package / Case	780-BFBGA, FCBGA
Supplier Device Package	780-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/ls1088axe7q1a

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

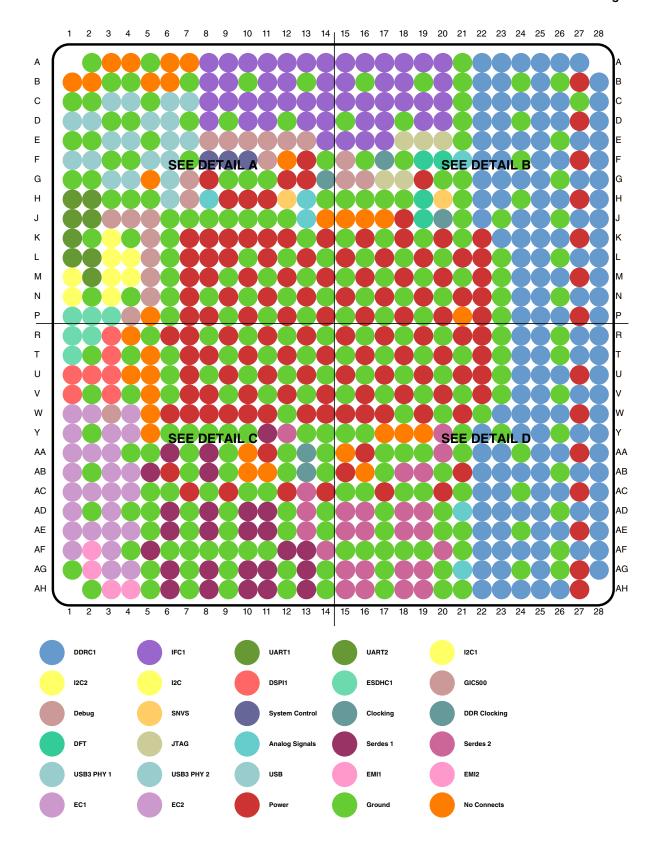


Figure 2. Complete BGA Map for the LS1088A

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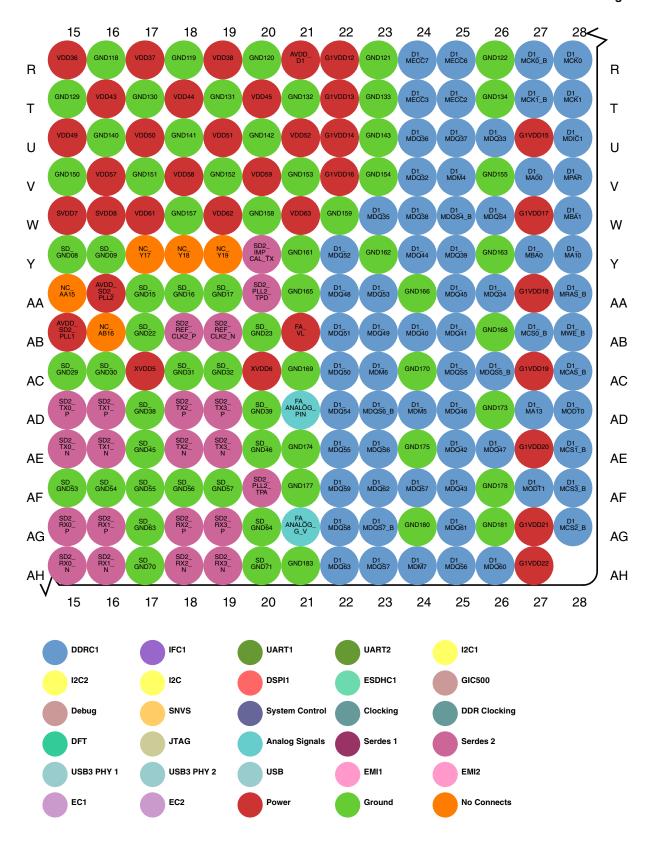


Figure 6. Detail D

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Table 1. Pinout list by bus (continued)

Signal	Signal description	Package	Pin	Power supply	Notes
		pin number	type		
D1_MCS3_B	Chip Select	AF28	0	G1V _{DD}	1
D1_MDIC0	Driver Impedence Calibration	P28	Ю	G1V _{DD}	3
D1_MDIC1	Driver Impedence Calibration	U28	Ю	G1V _{DD}	3
D1_MDM0	Data Mask	B23	0	G1V _{DD}	
D1_MDM1	Data Mask	H22	0	G1V _{DD}	
D1_MDM2	Data Mask	E25	0	G1V _{DD}	
D1_MDM3	Data Mask	J25	0	G1V _{DD}	
D1_MDM4	Data Mask	V25	0	G1V _{DD}	
D1_MDM5	Data Mask	AD24	0	G1V _{DD}	
D1_MDM6	Data Mask	AC23	0	G1V _{DD}	
D1_MDM7	Data Mask	AH24	0	G1V _{DD}	
D1_MDM8	Data Mask	P24	0	G1V _{DD}	
D1_MDQ00	Data	C22	Ю	G1V _{DD}	
D1_MDQ01	Data	A23	Ю	G1V _{DD}	
D1_MDQ02	Data	C26	Ю	G1V _{DD}	
D1_MDQ03	Data	A27	Ю	G1V _{DD}	
D1_MDQ04	Data	B22	Ю	G1V _{DD}	
D1_MDQ05	Data	A22	Ю	G1V _{DD}	
D1_MDQ06	Data	B25	Ю	G1V _{DD}	
D1_MDQ07	Data	A26	Ю	G1V _{DD}	
D1_MDQ08	Data	E22	Ю	G1V _{DD}	
D1_MDQ09	Data	D22	Ю	G1V _{DD}	
D1_MDQ10	Data	F23	Ю	G1V _{DD}	
D1_MDQ11	Data	G23	Ю	G1V _{DD}	
D1_MDQ12	Data	G22	Ю	G1V _{DD}	
D1_MDQ13	Data	F22	Ю	G1V _{DD}	
D1_MDQ14	Data	C24	Ю	G1V _{DD}	
D1_MDQ15	Data	E23	Ю	G1V _{DD}	
D1_MDQ16	Data	D26	Ю	G1V _{DD}	
D1_MDQ17	Data	E24	Ю	G1V _{DD}	
D1_MDQ18	Data	G24	Ю	G1V _{DD}	
D1_MDQ19	Data	H25	Ю	G1V _{DD}	
D1_MDQ20	Data	C25	Ю	G1V _{DD}	
D1_MDQ21	Data	D25	Ю	G1V _{DD}	
D1_MDQ22	Data	G25	Ю	G1V _{DD}	
D1_MDQ23	Data	H26	Ю	G1V _{DD}	
D1_MDQ24	Data	K23	Ю	G1V _{DD}	
D1_MDQ25	Data	J24	Ю	G1V _{DD}	

Table 1. Pinout list by bus (continued)

Signal	Signal description	Package pin number	Pin type	Power supply	Notes
DIFF_SYSCLK_B	Single Source System Clock Differential (negative)	AB13	I	SV _{DD}	20
RTC/GPIO3_30	Real Time Clock	F17	I	OV_{DD}	1
SYSCLK	System Clock	G14	I	OV _{DD}	
	DDR Clocki	ng			
DDRCLK	DDR Controller Clock	J20	I	OV _{DD}	
	DFT				
JTAG_BSR_VSEL	Reserved	J19	I	OV _{DD}	15
SCAN_MODE_B	Reserved	H19	I	OV _{DD}	10
TBSCAN_EN_B	Test Boundary Scan Enable	F19	ı	OV _{DD}	6
TEST_SEL_B	Reserved	F20	I	OV _{DD}	10
	JTAG		<u> </u>	1	
TCK	Test Clock	E18	ı	OV _{DD}	
TDI	Test Data In	G17	ı	OV _{DD}	9
TDO	Test Data Out	E20	0	OV _{DD}	2
TMS	Test Mode Select	G18	ı	OV _{DD}	9
TRST_B	Test Reset	E19	1	OV _{DD}	9
	Analog Sign				
D1_TPA	Reserved	F21	Ю		12
FA_ANALOG_G_V	Reserved	AG21	Ю		15
FA_ANALOG_PIN	Reserved	AD21	Ю		15
TD1_ANODE	Thermal diode anode	J13	Ю		17
TD1_CATHODE	Thermal diode cathode	H13	10		17
TH_TPA	Reserved	H8	-	-	12
_	SerDes 1			1	
SD1_IMP_CAL_RX	SerDes Receive Impedence Calibration	Y11	I	SV _{DD}	11
SD1_IMP_CAL_TX	SerDes Transmit Impedance Calibration	AA6	I	XV_{DD}	16
SD1_PLL1_TPA	SerDes PLL 1 Test Point Analog	AF12	0	AVDD_SD1_PLL1	12
SD1_PLL1_TPD	SerDes Test Point Digital	AF13	0	XV_{DD}	12
SD1_PLL2_TPA	SerDes PLL 2 Test Point Analog	AF5	0	AVDD_SD1_PLL2	12
SD1_PLL2_TPD	SerDes Test Point Digital	AB5	0	XV_{DD}	12
SD1_REF_CLK1_N	SerDes PLL 1 Reference Clock Complement	AH13	I	SV _{DD}	
SD1_REF_CLK1_P	SerDes PLL 1 Reference Clock	AG13	I	SV _{DD}	
SD1_REF_CLK2_N	SerDes PLL 2 Reference Clock Complement	AB8	I	SV _{DD}	

Table 1. Pinout list by bus (continued)

Cianal	Pin	Power cumply	Notes		
Signal	Signal description	Signal description Package pin number		Power supply	Notes
EC1_RXD2/GPIO2_30	Receive Data	Y1	I	LV _{DD}	1
EC1_RXD3/GPIO2_29	Receive Data	W2	I	LV _{DD}	1
EC1_RX_CLK/GPIO4_13	Receive Clock	W1	I	LV _{DD}	1
EC1_RX_DV/GPIO4_14	Receive Data Valid	AB1	ı	LV _{DD}	1
EC1_TXD0/GPIO2_25	Transmit Data	AB3	0	LV _{DD}	1
EC1_TXD1/GPIO2_24	Transmit Data	AA3	0	LV _{DD}	1
EC1_TXD2/GPIO2_23	Transmit Data	Y4	0	LV _{DD}	1
EC1_TXD3/GPIO2_22	Transmit Data	Y3	0	LV _{DD}	1
EC1_TX_EN/GPIO2_26	Transmit Enable	AB4	0	LV _{DD}	1, 14
	Ethernet Contr	oller 2		•	<u>'</u>
EC2_GTX_CLK/GPIO4_20	Transmit Clock Out	AC4	0	LV _{DD}	1
EC2_GTX_CLK125/GPIO4_21	Reference Clock	AG4	I	LV _{DD}	1
EC2_RXD0/GPIO4_25/ TSEC_1588_TRIG_IN2	Receive Data	AE2	I	LV _{DD}	1
EC2_RXD1/GPIO4_24/ TSEC_1588_PULSE_OUT1	Receive Data	AE1 I LV _{DD}		LV _{DD}	1
EC2_RXD2/GPIO4_23	Receive Data	AD1 I LV _{DD}		LV _{DD}	1
EC2_RXD3/GPIO4_22	Receive Data	AC2	I	LV _{DD}	1
EC2_RX_CLK/GPIO4_26/ TSEC_1588_CLK_IN	Receive Clock	AC1	I	LV _{DD}	1
EC2_RX_DV/GPIO4_27/ TSEC_1588_TRIG_IN1	Receive Data Valid	AF1	I	LV _{DD}	1
EC2_TXD0/GPIO4_18/ TSEC_1588_PULSE_OUT2	Transmit Data	AF3	0	LV _{DD}	1
EC2_TXD1/GPIO4_17/ TSEC_1588_CLK_OUT	Transmit Data	AE4	0	LV _{DD}	1
EC2_TXD2/GPIO4_16/ TSEC_1588_ALARM_OUT1	Transmit Data	AE3	0	LV _{DD}	1
EC2_TXD3/GPIO4_15/ TSEC_1588_ALARM_OUT2	Transmit Data	AD3	0	LV _{DD}	1
EC2_TX_EN/GPIO4_19	Transmit Enable	AG3	0	LV _{DD}	1, 14
	General Purpose In	put/Output			
GPIO1_00/ IFC_AD00 / cfg_gpinput0	General Purpose Input/Output	B12	0	OV _{DD}	1, 4
GPIO1_01/ IFC_AD01 / cfg_gpinput1	General Purpose Input/Output	A11	0	OV _{DD}	1, 4
GPIO1_02/ IFC_AD02 / cfg_gpinput2	General Purpose Input/Output	B11	0	OV _{DD}	1, 4
GPIO1_03/IFC_AD03/ cfg_gpinput3	General Purpose Input/Output	A10	0	OV _{DD}	1, 4
GPIO1_04/ IFC_AD04 / cfg_gpinput4	General Purpose Input/Output	A9	0	OV _{DD}	1, 4

Pin assignments

Table 1. Pinout list by bus (continued)

Signal	Signal description	Package pin number	Pin type	Power supply	Notes
GND141	Core, Platform and PLL Ground	U18			
GND142	Core, Platform and PLL Ground	U20			
GND143	Core, Platform and PLL Ground	U23			
GND144	Core, Platform and PLL Ground	V2			
GND145	Core, Platform and PLL Ground	V4			
GND146	Core, Platform and PLL Ground	V6			
GND147	Core, Platform and PLL Ground	V9			
GND148	Core, Platform and PLL Ground	V11			
GND149	Core, Platform and PLL Ground	V13			
GND150	Core, Platform and PLL Ground	V15			
GND151	Core, Platform and PLL Ground	V17			
GND152	Core, Platform and PLL Ground	V19			
GND153	Core, Platform and PLL Ground	V21			
GND154	Core, Platform and PLL Ground	V23			
GND155	Core, Platform and PLL Ground	V26			
GND156	Core, Platform and PLL Ground	W12			
GND157	Core, Platform and PLL Ground	W18			
GND158	Core, Platform and PLL Ground	W20			
GND159	Core, Platform and PLL Ground	W22			
GND160	Core, Platform and PLL Ground	Y2			
GND161	Core, Platform and PLL Ground	Y21			
GND162	Core, Platform and PLL Ground	Y23			

Pin assignments

Table 1. Pinout list by bus (continued)

Signal	Signal description	Package pin number	Pin type	Power supply	Notes
SD_GND46	SerDes core logic, transceiver, and PLL ground	AE20			18
SD_GND47	SerDes core logic, transceiver, and PLL ground	AF6			18
SD_GND48	SerDes core logic, transceiver, and PLL ground	AF7			18
SD_GND49	SerDes core logic, transceiver, and PLL ground	AF8			18
SD_GND50	SerDes core logic, transceiver, and PLL ground	AF9			18
SD_GND51	SerDes core logic, transceiver, and PLL ground	AF10			18
SD_GND52	SerDes core logic, transceiver, and PLL ground	AF11			18
SD_GND53	SerDes core logic, transceiver, and PLL ground	AF15			18
SD_GND54	SerDes core logic, transceiver, and PLL ground	AF16			18
SD_GND55	SerDes core logic, transceiver, and PLL ground	AF17			18
SD_GND56	SerDes core logic, transceiver, and PLL ground	AF18			18
SD_GND57	SerDes core logic, transceiver, and PLL ground	AF19			18
SD_GND58	SerDes core logic, transceiver, and PLL ground	AG5			18
SD_GND59	SerDes core logic, transceiver, and PLL ground	AG7			18
SD_GND60	SerDes core logic, transceiver, and PLL ground	AG9			18
SD_GND61	SerDes core logic, transceiver, and PLL ground	AG12			18
SD_GND62	SerDes core logic, transceiver, and PLL ground	AG14			18
SD_GND63	SerDes core logic, transceiver, and PLL ground	AG17			18
SD_GND64	SerDes core logic, transceiver, and PLL ground	AG20			18
SD_GND65	SerDes core logic, transceiver, and PLL ground	AH5			18
SD_GND66	SerDes core logic, transceiver, and PLL ground	AH7			18
SD_GND67	SerDes core logic, transceiver, and PLL ground	AH9			18

Electrical characteristics

adjust the memory clocks by ½ applied cycle for data rates of 1866 MT/s or less and 9/16 applied cycle for data rates greater than 1866 MT/s. It is recommended that, during system validation, memory clocks are adjusted to best fit the particular system design.

This figure shows the DDR4 SDRAM interface output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

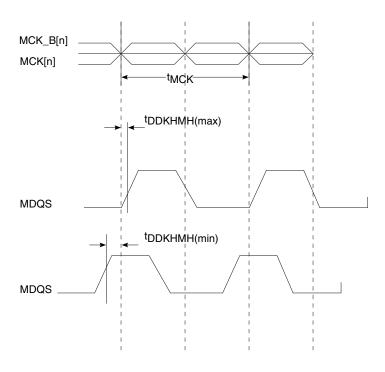


Figure 12. t_{DDKHMH} timing diagram

This figure shows the DDR4 SDRAM output timing diagram.

3.12 Enhanced secure digital host controller (eSDHC)

This section describes the DC and AC electrical specifications for the eSDHC interface.

3.12.1 eSDHC DC electrical characteristics

This table provides the DC electrical characteristics for the eSDHC interface.

Table 33. eSDHC interface DC electrical characteristics (E/DV_{DD}=3.3 V)³

Characteristic	Symbol	Min	Max	Unit	Notes
Input high voltage	V _{IH}	0.7 x E/DV _{DD}	-	V	1
Input low voltage	V _{IL}	-	0.25 x E/DV _{DD}	V	1
Output high voltage	V _{OH}	0.75 x E/DV _{DD}	-	V	-
(I _{OH} = -100 μA at E/DV _{DD} min)					
Output low voltage	V _{OL}	-	0.125 x E/DV _{DD}	V	-
(I_{OL} = 100 μA at E/DV _{DD} min)					
Output high voltage	V _{OH}	E/DV _{DD} - 0.2	-	V	2
$(I_{OH} = -100 \mu A)$					
Output low voltage	V _{OL}	-	0.3	V	2
$(I_{OL} = 2 \text{ mA})$					
Input/output leakage current	(I _{IN} /I _{OZ})	-10	10	μΑ	2

Notes:

Table 34. eSDHC interface DC electrical characteristics (E/D/OV_{DD}=1.8 V)³

Characteristic	Symbol	Min	Max	Unit	Notes
Input high voltage	V _{IH}	0.7 x E/D/OV _{DD}	-	V	1
Input low voltage	V _{IL}	-	0.3 x E/D/OV _{DD}	V	1
Output high voltage	V _{OH}	E/D/OV _{DD} - 0.45	-	V	-
(I _{OH} = -2 mA at E/D/OV _{DD} min)					
Output low voltage	V _{OL}	-	0.45	V	-
(I _{OL} = 2 mA at EV _{DD} min)					
Output high voltage	V _{OH}	E/D/OV _{DD} - 0.2	-	V	2
$I_{OH} = -100 \mu A$					
Output low voltage	V _{OL}	-	0.3	V	2
(I _{OL} = 2 mA)					

Table continues on the next page...

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^{1.} The min V_{IL} and max V_{IH} values are based on the respective min and max EV_{IN} values found in the Table 3.

^{2.} Open-drain mode is for MMC cards only.

^{3.} At recommended operating conditions with $E/DV_{DD} = 3.3 \text{ V}$.

3.14.1 GPIO DC electrical characteristics

This table provides the DC electrical characteristics for the GPIO interface operating at $D/EV_{DD} = 3.3 \text{ V}$.

Table 52. GPIO DC electrical characteristics $(D/EV_{DD} = 3.3 \text{ V})^1$

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage	V _{IH}	0.7 x D/EV _{DD}	-	V	2
Input low voltage	V _{IL}	-	0.2 x D/EV _{DD}	V	2
Input current (V _{IN} = 0V or V _{IN} = LV _{DD})	I _{IN}	-	±50	μΑ	3
Output high voltage (D/EV _{DD} = min, I _{OH} = -2 mA)	V _{OH}	2.4	-	V	-
Output low voltage (D/EV _{DD} = min, $I_{OL} = 2$ mA)	V _{OL}	-	0.4	V	-

^{1.} For recommended operating conditions, see Table 3.

This table provides the DC electrical characteristics for the GPIO interface operating at $TV_{DD} = 2.5 \text{ V}$.

Table 53. GPIO DC electrical characteristics $(TV_{DD} = 2.5 \text{ V})^1$

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage	V _{IH}	0.7 x TV _{DD}	-	V	2
Input low voltage	V _{IL}	-	0.2 x TV _{DD}	V	2
Input current (V _{IN} = 0V or V _{IN} = LV _{DD})	I _{IN}	-	±50	μΑ	3
Output high voltage (TV _{DD} = min, $I_{OH} = -1$ mA)	V _{OH}	2.0	-	V	-
Output low voltage (TV _{DD} = min, I _{OL} = 1 mA)	V _{OL}	-	0.4	V	-

^{1.} For recommended operating conditions, see Table 3.

This table provides the DC electrical characteristics for the GPIO interface operating at $D/E/TV_{DD} = 1.8 \text{ V}$.

Table 54. GPIO DC electrical characteristics $(D/E/TV_{DD} = 1.8 \text{ V})^1$

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage	V _{IH}	0.7 x D/E/TV _{DD}	-	V	2

Table continues on the next page...

^{2.} The min V_{IL} and max V_{IH} values are based on the respective min and max DV_{IN}/EV_{IN} values found in Table 3.

^{3.} The symbol DV_{IN}/EV_{IN} represents the input voltage of the supply referenced in Table 3.

^{2.} The min V_{IL} and max V_{IH} values are based on the respective min and max TV_{IN} values found in Table 3.

^{3.} The symbol TV_{IN} represents the input voltage of the supply referenced in Table 3.

Electrical characteristics

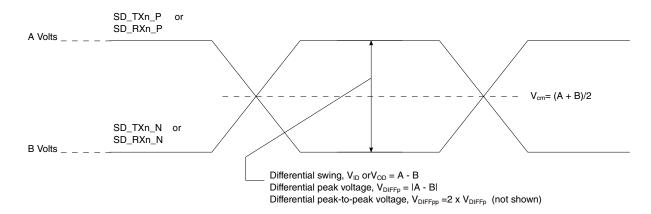


Figure 29. Differential voltage definitions for transmitter or receiver

Using this waveform, the definitions are as described in the following list. To simplify the illustration, the definitions assume that the SerDes transmitter and receiver operate in a fully symmetrical differential signaling environment:

Single-Ended Swing

The transmitter output signals and the receiver input signals SD_TXn_P , SD_TXn_N , SD_RXn_P and SD_RXn_N each have a peak-to-peak swing of A - B volts. This is also referred to as each signal wire's single-ended swing.

Differential Output Voltage, V_{OD} (or Differential Output Swing)

The differential output voltage (or swing) of the transmitter, V_{OD} , is defined as the difference of the two complementary output voltages: $V_{SD_TXn_P} - V_{SD_TXn_N}$. The V_{OD} value can be either positive or negative.

Differential Input Voltage, V_{ID} (or Differential Input Swing)

The differential input voltage (or swing) of the receiver, V_{ID} , is defined as the difference of the two complementary input voltages: $V_{SD_RXn_P}$ - $V_{SD_RXn_N}$. The V_{ID} value can be either positive or negative.

Differential Peak Voltage, V_{DIFFp}

The peak value of the differential transmitter output signal or the differential receiver input signal is defined as the differential peak voltage, $V_{DIFFp} = |A - B|$ volts.

Differential Peak-to-Peak, $V_{DIFFp-p}$

Because the differential output signal of the transmitter and the differential input signal of the receiver each range from A - B to -(A - B) volts, the peak-to-peak value of the differential transmitter output signal or the differential receiver input signal is defined as differential peak-to-peak voltage, $V_{DIFFp-p} = 2 \times V_{DIFFp} = 2 \times |(A - B)|$ volts, which is twice the differential swing in amplitude, or twice the differential peak. For example, the output differential peak-to-peak voltage can also be calculated as $V_{TX-DIFFp-p} = 2 \times |V_{OD}|$.

Differential Waveform

The differential waveform is constructed by subtracting the inverting signal (SD_TX*n*_N, for example) from the non-inverting signal (SD_TX*n*_P, for example)

Table 69. PCI Express 3.0 (8 GT/s) differential transmitter output DC characteristics ($XV_{DD} = 1.35 \text{ V}$)³

Parameter	Symbol	Min	Typical	Max	Units	Notes
Full swing transmitter voltage with no TX Eq	V _{TX-FS-NO-EQ}	800	_	1300	mVp-p	See Note 1.
Reduced swing transmitter voltage with no TX Eq	V _{TX-RS-NO-EQ}	400	_	1300	mV	See Note 1.
De-emphasized differential output voltage (ratio)	V _{TX-DE-RATIO-3.5dB}	3.0	3.5	4.0	dB	_
De-emphasized differential output voltage (ratio)	V _{TX-DE-RATIO-6.0dB}	5.5	6.0	6.5	dB	_
Minimum swing during EIEOS for full swing	V _{TX-EIEOS-FS}	250	_	_	mVp-p	See Note 2
Minimum swing during EIEOS for reduced swing	V _{TX-EIEOS-RS}	232	_	_	mVp-p	See Note 2
DC differential transmitter impedance	Z _{TX-DIFF-DC}	80	100	120	Ω	Transmitter DC differential mode low impedance
Transmitter DC Impedance	Z _{TX-DC}	40	50	60	Ω	Required transmitter D+ as well as D- DC impedance during all states

Notes:

3.16.4.3.2 PCI Express DC physical layer receiver specifications

This section discusses the PCI Express DC physical layer receiver specifications for 2.5 GT/s, 5 GT/s, and 8 GT/s.

This table defines the DC specifications for the PCI Express 2.0 (2.5 GT/s) differential input at all receivers. The parameters are specified at the component pins.

Table 70. PCI Express 2.0 (2.5 GT/s) differential receiver input DC specifications (SV_{DD} = $0.9V/1.0 V)^4$

Parameter	Symbol	Min	Тур	Max	Units	Notes
Differential input peak-to-peak	V _{RX-DIFFp-p}	175	1000	1200	mV	$V_{RX-DIFFp-p} = 2 \times V_{RX-D+} - V_{RX-D-} $ See
voltage						Note 1.

Table continues on the next page...

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^{1.} Voltage measurements for $V_{TX\text{-FS-NO-EQ}}$ and $V_{TX\text{-RS-NO-EQ}}$ are made using the 64-zeroes/64-ones pattern in the compliance pattern.

^{2.} Voltage limits comprehend both full swing and reduced swing modes. The transmitter must reject any changes that would violate this specification. The maximum level is covered in the $V_{TX-FS-NO-EQ}$ measurement which represents the maximum peak voltage the transmitter can drive. The $V_{TX-EIEOS-FS}$ and $V_{TX-EIEOS-RS}$ voltage limits are imposed to guarantee the EIEOS threshold of 175 mV_{P-P} at the receiver pin. This parameter is measured using the actual EIEOS pattern that is part of the compliance pattern and then removing the ISI contribution of the breakout channel.

^{3.} For recommended operating conditions, see Table 3.

3.16.8.3 XFI AC timing specifications

NOTE

The AC specifications do not include RefClk jitter.

This table defines the XFI transmitter AC timing specifications.

Table 104. XFI transmitter AC timing specifications

Parameter	Symbol	Min	Тур	Max	Unit
Transmitter baud Rate	T _{BAUD}	10.3125-100ppm	10.3125	10.3125+100ppm	Gb/s
Unit Interval	UI	-	96.96	-	ps
Deterministic jitter	DJ	-	-	0.15	UI p-p
Total jitter tolerance	T _J	-	-	0.3	UI p-p

This table defines the XFI receiver AC timing specifications. RefClk jitter is not included.

Table 105. XFI receiver AC timing specifications

Parameter	Symbol	Min	Тур	Max	Unit	Notes
Unit Interval	UI	-	96.96	-	ps	-
Receiver baud rate	R _{BAUD}	10.3125-100ppm	10.3125	10.3125+100ppm	Gb/s	-
Total non-EQJ jitter	T _{NON-EQJ}	-	-	0.45	UI p-p	1
Total jitter tolerance	T _J	-	-	0.65	UI p-p	1, 2

^{1.} The total jitter (TJ) consists of Random Jitter (RJ), Duty Cycle Distortion (DCD), Periodic Jitter (PJ), and Inter-Symbol Interference (ISI). Non-EQJ jitter can include duty cycle distortion (DCD), random jitter (RJ), and periodic jitter (PJ). Non-EQJ jitter is uncorrelated to the primary data stream with exception of the DCD and so cannot be equalized by the receiver under test. It can exhibit a wide spectrum. Non - EQJ = TJ - ISI = RJ + DCD + PJ.

This figure shows the sinusoidal jitter tolerance of XFI receiver.

^{2.} The XFI channel has a loss budget of 9.6 dB @5.5GHz. The channel loss including connector @ 5.5GHz is 6dB. The channel crosstalk and reflection margin is 3.6dB. Manual tuning of TX Equalization and amplitude will be required for performance optimization.

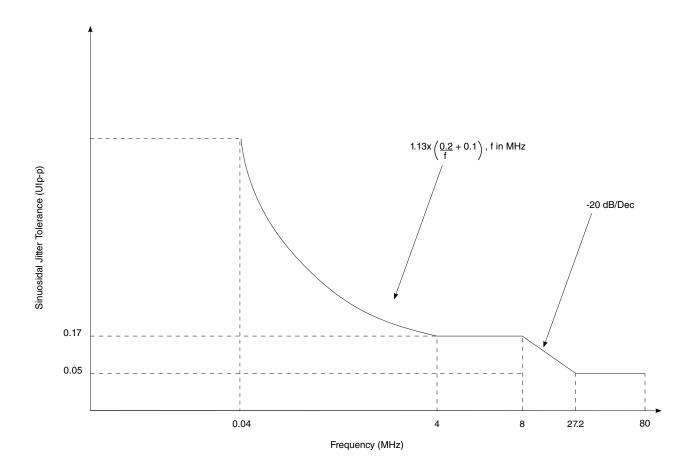


Figure 44. XFI host receiver input sinusoidal jitter tolerance

3.16.9 1000Base-KX interface

This section describes the electrical characteristics for the 1000Base-KX interface. Only AC-coupled operation is supported.

3.16.9.1 1000Base-KX DC electrical characteristics

This table describes the 1000Base-KX SerDes transmitter DC electrical characteristics at TP1 per IEEE Std 802.3ap-2007. Transmitter DC electrical characteristics are measured at the transmitter outputs (SDn_TXn_P and SDn_TXn_N).

Table 106. 1000Base-KX transmitter DC electrical characteristics¹

Parameter	Symbol	Min	Тур	Max	Unit	Notes
Output differential voltage	V _{TX-DIFFp-p}	800.0	-	1600.0	mV	2

Table continues on the next page...

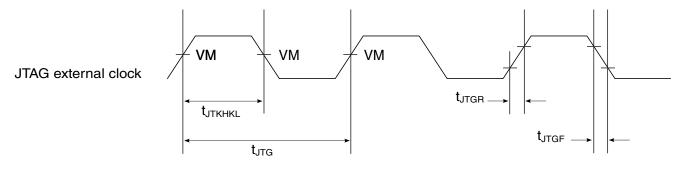
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Electrical characteristics

Table 125. Integrated flash controller IFC-NAND NVDDR interface AC timing specifications (OVDD = 1.8 V) (continued)

Parameter	Symbol	I/O	Min	Max	Unit	Notes
Command, Address, Data delay (command to command, address to address, command to address, address to command, command/ address to start of data) Fast	tCADf	О	TCAD - 150 (ps)	TCAD + 150 (ps)	t _{IP_CLK}	Figure 68
Command, Address, Data delay (command to command, address to address, command to address, address to command, command/ address to start of data) slow	tCADs	О	TCAD - 150 (ps)	TCAD + 150 (ps)	t _{IP_CLK}	Figure 68
Command/address DQ hold time	t _{CAH}	0	2 + 150 (ps)	-	ns	Figure 68
CLE and ALE hold time	t _{CALH}	0	2 + 150 (ps)	-	ns	Figure 68
CLE and ALE setup time	t _{CALS}	0	2 + 150 (ps)	-	ns	Figure 68
Command/address DQ setup time	t _{CAS}	0	2 + 150 (ps)	-	ns	Figure 68
CE# hold time	t _{CH}	0	2 + 150 (ps)	-	ns	Figure 68
Average clock cycle time, also known as tCK	t _{CK} (avg) or t _{CK}	0	10	-	ns	Figure 68
Absolute clock period, measured from rising edge to the next consecutive rising edge	t _{CK} (abs)	О	tCK(avg) + tJIT(per) min	tCK(avg) + tJIT(per) max	ns	Figure 68
Clock cycle high	t _{CKH} (abs)	0	0.45	0.55	tCK	Figure 68
Clock cycle low	t _{CKL} (abs)	0	0.45	0.55	tCK	Figure 68
Data input end to W/R# high B16	t _{CKWR}	0	TCKWR - 150 (ps)	TCKWR + 150 (ps)	t _{IP_CLK}	Figure 71
CE# setup time	t _{CS}	0	TCS - 150 (ps)	TCS + 150 (ps)	t _{IP_CLK}	Figure 70
Data DQ hold time	t _{DH}	0	1050	-	ps	Figure 70
Access window of DQS from CLK	tDQSCK	I	-	20 + 150 (ps)	ns	Figure 71
W/R# low to DQS/DQ driven by device	t _{DQSD}	I	-150 (ps)	18 + 150 (ps)	ns	Figure 71
DQS output high pulse width	t _{DQSH}	0	0.45	0.55	tCK	Figure 70
W/R# high to DQS/DQ tri- state by device	t _{DQSHZ}	0	RHZ - 150 (ps)	RHZ + 150 (ps)	t _{IP_CLK}	Figure 68
DQS output low pulse width	t _{DQSL}	0	0.45	0.55	tCK	Figure 70

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VM = Midpoint voltage (OV_{DD}/2)

Figure 79. JTAG clock input timing diagram

This figure shows the TRST_B timing diagram.

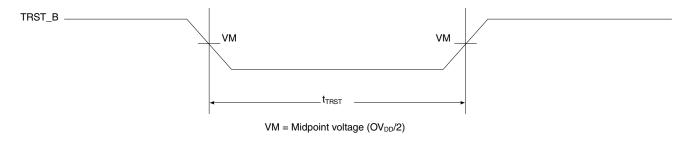


Figure 80. TRST_B timing diagram

This figure shows the boundary-scan timing diagram.

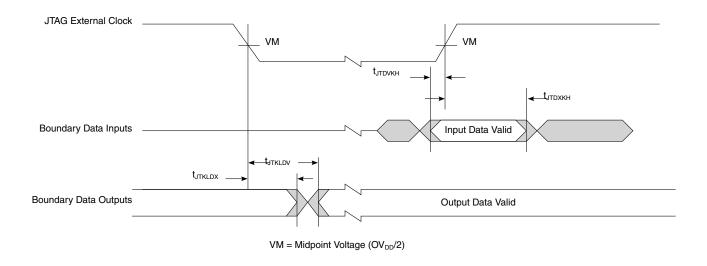


Figure 81. Boundary-scan timing diagram

3.20 Quad serial peripheral interface (QuadSPI)

This section describes the DC and AC electrical characteristics for the QuadSPI interface.

3.20.1 QuadSPI DC electrical characteristics

This table provides the DC electrical characteristics for the QuadSPI interface operating at $OV_{DD} = 1.8V$.

Table 128. QuadSPI DC electrical characteristics¹

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage	V _{IH}	0.7 x OV _{DD}	-	V	2
Input low voltage	V _{IL}	-	0.3 x OV _{DD}	V	2
Input current $(0V \le V_{IN} \le OV_{DD})$	I _{IN}	-	±50	μΑ	3
Output high voltage (OV _{DD} = min, I_{OH} = -100 μ A)	V _{OH}	OV _{DD} - 0.2	-	V	-
Output low voltage (OV _{DD} = min, I_{OL} = 100 μ A)	V _{OL}	-	0.2	V	-

^{1.} For recommended operating conditions, see Table 3.

3.20.2 QuadSPI AC timing specifications

This section describes the QuadSPI timing specifications in both SDR and DDR modes. All data is based on a negative edge data launch from the device and a positive edge data capture, as shown in the timing figures in this section.

This table provides the QuadSPI input and output timing in SDR mode (MCR[DQS_EN] = 0, regarding to the 1st sample point. See qSPI_SMPR[xSDLY, xSPHS] in the corresponding chip reference manual for different sampling points). Note that T represents the clock period, j represents qSPI_FLSHCR[TCSH], and k depends on qSPI_FLSHCR[TCSS].

Table 129. QuadSPI SDR mode input and output timing

Parameter	Symbol	Min	Max	Unit
Clock rise/fall time	T _{RISE} /T _{FALL}	1.0	-	ns
CS output hold time	t _{NIKHOX2}	-3.3 + j * T	-	ns
CS output delay	t _{NIKHOV2}	-3.0 + k * T	-	ns

Table continues on the next page...

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^{2.} The min VIL and max VIH values are based on the respective min and max OVIN values found in Table 3.

^{3.} Note that the symbol OV_{IN} represents the input voltage of the supply referenced in the Recommended Operating Conditions table.

Electrical characteristics

This table provides the QuadSPI input and output timing in DDR mode with external DQS/delay chain (MCR[DQS_EN] = 1, regarding to the 1st sample point). Note that T represents the clock period, j depends on the value of qSPI_FLSHCR[TCSH], k depends on qSPI_FLSHCR[TCSS], and m depends on QSPI_FLSHCR[TDH].

Parameter	Symbol	Min	Max	Unit
Clock rise/fall time	T _{RISE} /T _{FALL}	1.0	-	ns
CS output hold time	t _{NIKHOX2}	3.3 + T * j	-	ns
CS output delay	t _{NIKHOV2}	-3.0 + k * T		ns
DQS to data skew	t _{NIDSH} /t _{NIIDSL}	-0.9	0.9	ns
Output data valid	t _{NIKHOV}	-	0.9 + m * T/8	ns
Output data hold	t _{NIKHOX}	-0.9 + m * T/8	-	ns

Table 131. QuadSPI DDR mode input and output timing

This figure shows the QuadSPI AC timing in DDR mode.

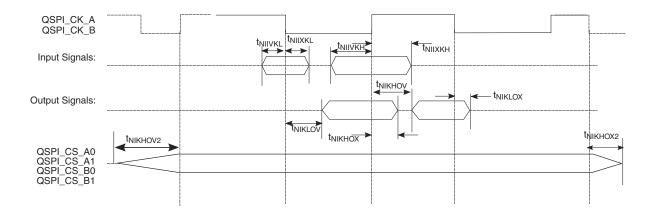


Figure 83. QuadSPI AC timing — DDR mode

This figure shows the QuadSPI data input timing in DDR mode with an external DQS.

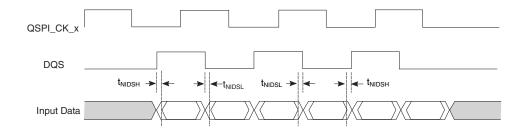


Figure 84. QuadSPI input AC timing — DDR mode with an external DQS

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Table 147. Processor, platform, and memory clocking specifications

Characteristic	Maximum processor core frequency						Unit	Notes
	1200 MHz		1400 MHz		1600 MHz			
	Min	Max	Min	Max	Min	Max		
Core cluster group PLL frequency	600	1200	600	1400	600	1600	MHz	1
Platform clock frequency	400	500	400	600	400	700	MHz	1
Memory bus clock frequency	650	800	650	900	650	1050	MHz	1, 2
IFC clock frequency	-	100	-	100	-	100	MHz	3

^{1.} **Caution:**The coherency domain clock to SYSCLK ratio and core to SYSCLK ratio settings must be chosen such that the resulting SYSCLK frequency, core frequency, coherency domain and platform clock frequency do not exceed their respective maximum or minimum operating frequencies.

4.2 Power supply design

For additional details on the power supply design, see AN5144, QorIQ LS1088A Design Checklist.

4.2.1 Voltage ID (VID) controllable supply

To guarantee performance and power specifications, a specific method of selecting the optimum voltage-level must be implemented when the chip is used. As part of the chip's boot process, software must read the VID efuse values stored in the Fuse Status register (FUSESR) and then configure the external voltage regulator based on this information. This method requires a point of load voltage regulator for each chip. When VID option is used, the V_{DD} supply should be separated from the SerDes 1.0 V supply SnV_{DD}. It is required in order to control the V_{DD} supply only.

NOTE

During the power-on reset process, the fuse values are read and stored in the FUSESR. It is expected that the chip's boot code reads the FUSESR value very early in the boot sequence and updates the regulator accordingly.

The default voltage regulator setting that is safe for the system to boot is the recommended operating V_{DD} at initial start-up of 1.025 V. It is highly recommended to select a regulator with a Vout range of at least 0.9 V to 1.1 V, with a resolution of 12.5 mV or better, when implementing a VID solution.

^{2.} The memory bus clock speed is half the DDR4 data rate.

^{3.} The integrated flash controller (IFC) clock speed on IFC_CLK[0:1] is determined by the platform clock divided by the IFC ratio programmed in CCR[CLKDIV]. See the chip reference manual for more information.

Recommended thermal model 5.1

Information about Flotherm models of the package or thermal data not available in this document can be obtained from your local NXP sales office.

Temperature diode 5.2

The chip has a temperature diode on the microprocessor that can be used in conjunction with other system temperature monitoring devices (such as Analog Devices, ADT7461A). These devices feature series resistance cancellation using three current measurements, where up to 1.5 k Ω of resistance can be automatically cancelled from the temperature result, allowing noise filtering and a more accurate reading.

The following are the specifications of the chip's on-board temperature diode:

Operating range: TBD

Ideality factor TBD; Temperature range TBD

Thermal management information 5.3

This section provides thermal management information for the flip-chip, plastic-ball, grid array (FC-PBGA) package for air-cooled applications. Proper thermal control design is primarily dependent on the system-level design-the heat sink, airflow, and thermal interface material.

The recommended attachment method to the heat sink is illustrated in Figure 95. The heat sink should be attached to the printed-circuit board with the spring force centered over the die. This spring force should not exceed 15 pounds force.

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